

AOS Semiconductor Product Reliability Report

AOTF7N60FD, rev A

Plastic Encapsulated Device

ALPHA & OMEGA Semiconductor, Inc

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This AOS product reliability report summarizes the qualification result for AOTF7N60FD. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AOTF7N60FD passes AOS quality and reliability requirements. The released product will be categorized by the process family and be monitored on a quarterly basis for continuously improving the product quality.

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I. Product Description:

The AOTF7N60FD has been fabricated using an advanced high voltage MOSFET process that is designed to deliver high levels of performance and robustness in popular AC-DC applications. By providing low $R_{DS(on)}$, Ciss and Crss along with guaranteed avalanche capability this part can be adopted quickly into new and existing offline power supply designs.

Details refer to the datasheet.

II. Die / Package Information:

	AOTF7N60FD
Process	Standard sub-micron
	600V, 7A N-Channel MOSFET with Fast Recovery Diode
Package Type	TO220F
Lead Frame	Bare Cu
Die Attach	Soft solder
Bonding	Al wire
Mold Material	Epoxy resin with silica filler
Moisture Level	Up to Level 1 *
Note * based on info provi	ded by assembler and mold compound supplier



Test Item	Test Condition	Time	Lot	Total	Number	Reference
		Point	Attribution	Sample	of	Standard
				size	Failures	
MSL	168hr 85°c	-	12 lots	2112pcs	0	JESD22-
Precondition	/85%RH +3 cycle					A113
	reflow@260°c					
HTGB	Temp = 150°c ,	168hrs	2 lots	539pcs	0	JESD22-
	Vgs=100% of	500 hrs	3 lots			A108
	Vgsmax	1000 hrs	3 lots			
			(Note A*)	77 pcs / lot		
HTRB	Temp = 150°c ,	168hrs	2 lots	539pcs	0	JESD22-
	Vds=80% of	500 hrs	3 lots			A108
	Vdsmax	1000 hrs	3 lots			
			(Note A*)	77 pcs / lot		
HAST	130, 85%RH,	96 hrs	9 lots	495pcs	0	JESD22-
	33.3 psi, Vgs =			-		A110
	100% of Vgs max					
			(Note A*)	55 pcs / lot		
Pressure Pot	121°c , 29.7psi,	96 hrs	9 lots	693pcs	0	JESD22-
	RH=100%			77 noo / lot		A102
			(Note A [*])	// pcs/lot		
Temperature	-65°c to 150°c,	250 / 500	12 lots	924pcs	0	JESD22-
Cycle	air to air,	cycles				A104
			(Note A*)	77 pcs / lot		

Note A: The reliability data presents total of available generic data up to the published date.

IV. Reliability Evaluation

FIT rate (per billion): 4.73 MTTF = 23972 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size of the selected product (AOTF7N60FD). Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

Failure Rate = $Chi^2 \times 10^9 / [2 (N) (H) (Af)]$ = 1.83 x 10⁹ / [2x (4x77x168 +6x77x500 +6x77x1000) x258] = 4.73 MTTF = 10⁹ / FIT =2.10 x 10⁸ hrs = 23972 years

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval \mathbf{N} = Total Number of units from HTRB and HTGB tests

H = Duration of HTRB/HTGB testing

Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = $55^{\circ}C$) Acceleration Factor [**Af**] = **Exp** [Ea / k (1/Tj u - 1/Tj s)]

Acceleration Factor [At] = Exp [Ea / k (1/t] u - Acceleration Factor ratio list:

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C		
Af	258	87	32	13	5.64	2.59	1		

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16

Tj u =The use junction temperature in degree (Kelvin), K = C+273.16

 \mathbf{k} = Boltzmann's constant, 8.617164 X 10⁻⁵eV / K